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| SPEC SHEET (FOR REFERENCE) | SHEET No. | Rev. | Page. |
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TYPE : 6PT2206N3D**

| | |
|------------------------|--------------|
| CHIP SIZE | 0.4 * 0.4 mm |
| WAFER SIZE | 6 inch |
| POSSIBLE DIE PER WAFER | 95,200 pcs |

Maximum Ratings (Ta=25°C)

| Characteristics | Symbol | Ratings | Unit |
|----------------------|--------|---------|------|
| Drain-source voltage | VDSS | 60 | V |
| Gate-source voltage | VGSS | ±20 | V |
| Drain Current (DC) | ID | 0.3 | A |

* For Reference

WAFER PROBING SPEC (Ta=25°C)

| No | MODE | LIMIT | | | | CONDITIONS |
|----|----------|-------|-----|------|------|---------------------|
| | | MIN. | Typ | MAX. | UNIT | |
| 1 | IGSS | | | ±10 | uA | VGS= ±20V VDS= 0V |
| 2 | IDSS | | | 1 | uA | VDS= 60V VGS= 0V |
| 3 | BVDSS | 63 | | | V | ID= 10uA |
| 4 | VTH | 1.2 | 1.6 | 2.0 | V | ID= 250uA VDS=VGS |
| 5 | RDS(on)1 | | 1.4 | 2.0 | Ω | ID= 100mA VGS= 5.0V |
| 6 | RDS(on)2 | | 1.1 | 1.6 | Ω | ID= 500mA VGS= 10V |
| 7 | VSD | 0.5 | | 1.1 | V | I= 115mA VGS= 0V |

※ Built-in ZD between Gate and Source

TENTATIVE

NOTE: